RENESAS BCR8PM-12LD

Triac Medium Power Use

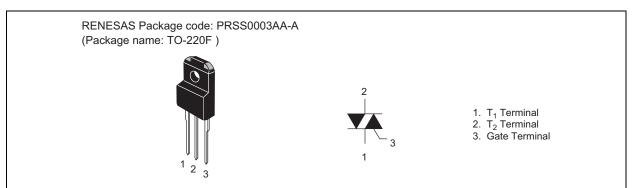
> REJ03G1564-0100 Rev.1.00 Jul 06, 2007

Features

- I_{T (RMS)} : 8 A
- V_{DRM} : 600 V
- I_{FGTI} , I_{RGTI} , I_{RGTIII} : 50 mA
- Viso : 2000 V

- The product guaranteed maximum junction temperature 150°C.
- Insulated Type
- Planar Type

Outline



Applications

Motor control, heater control

Maximum Ratings

Parameter	Symbol	Voltage class	Unit	
Falanielei	Symbol	12		
Repetitive peak off-state voltage ^{Note1}	V _{DRM}	600	V	
Non-repetitive peak off-state voltage ^{Note1}	V _{DSM}	700	V	

BCR8PM-12LD

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}			Commercial frequency, sine full wave 360° conduction, Tc = 85° C
Surge on-state current	I _{TSM}	48	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusing	l ² t	9.5	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P _{GM}	5	W	
Average gate power dissipation	P _{G (AV)}	0.5	W	
Peak gate voltage	V _{GM}	10	V	
Peak gate current	I _{GM}	2	А	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	2000	V	Ta = 25°C, AC 1 minute, T ₁ ·T ₂ ·G terminal to case

Notes: 1. Gate open.

Electrical Characteristics

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state cur	rent	I _{DRM}	—	_	2.0	mA	Tj = 125°C, V _{DRM} applied
On-state voltage		V _{TM}	_	—	2.0	V	$Tc = 25^{\circ}C$, $I_{TM} = 12 A$, Instantaneous measurement
Gate trigger voltage ^{Note2}	Ι	V_{FGTI}	_	_	1.5	V	$Tj=25^{\circ}C,\ V_D=6\ V,\ R_L=6\ \Omega,$
	II	V _{RGTI}	—	_	1.5	V	R _G = 330 Ω
	III	V _{RGTIII}	—	_	1.5	V	
Gate trigger current ^{Note2}	Ι	I _{FGTI}	—	—	50	mA	$Tj=25^{\circ}C,\ V_{D}=6\ V,\ R_{L}=6\ \Omega,$
	II	I _{RGTI}		_	50	mA	R _G = 330 Ω
	III	I _{RGTIII}	_	_	50	mA	
Gate non-trigger voltage		V_{GD}	0.2	_	_	V	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-c)}	_	_	4.9	°C/W	Junction to case ^{Note3}
Critical-rate of rise of off-stat commutating voltage ^{Note4}	te	(dv/dt)c	10	—	_	V/µs	Tj = 125°C

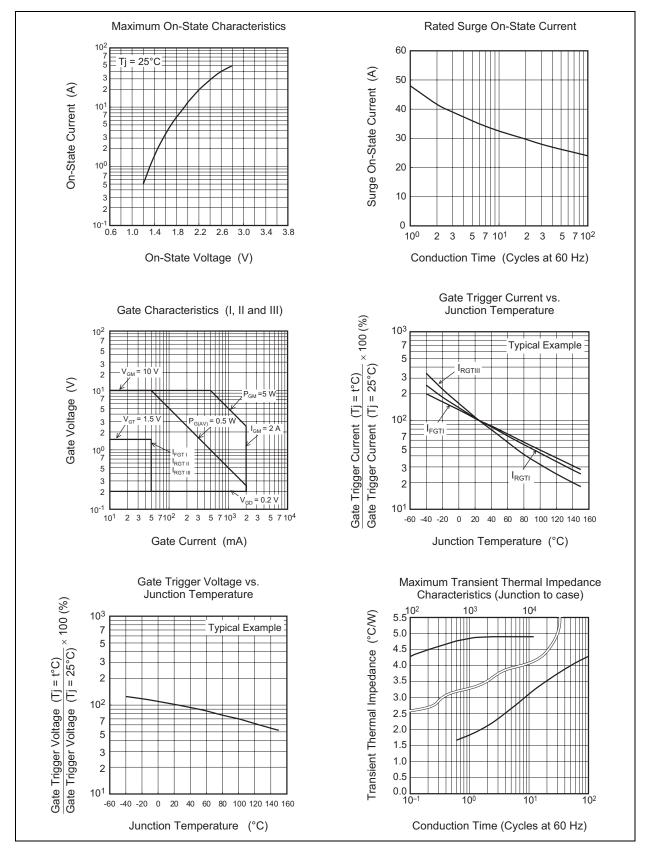
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance $R_{th\,(c\text{-}f)}$ in case of greasing is 0.5°C/W.

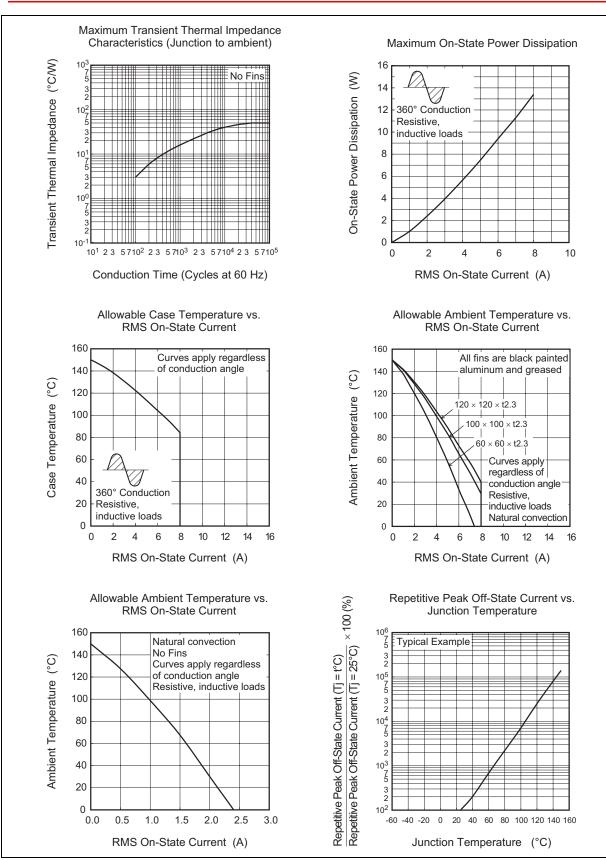
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C	Supply Voltage → Time
2. Rate of decay of on-state commutating current (di/dt)c = - 4 A/ms	Main Current → Time
3. Peak off-state voltage V _D = 400 V	Main Voltage → Time (dv/df)c V _D

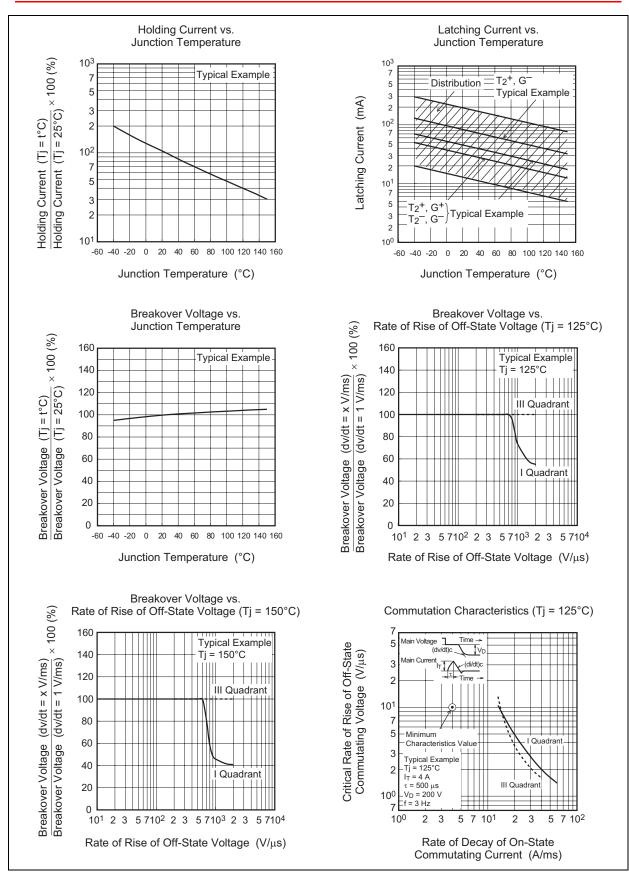
Performance Curves



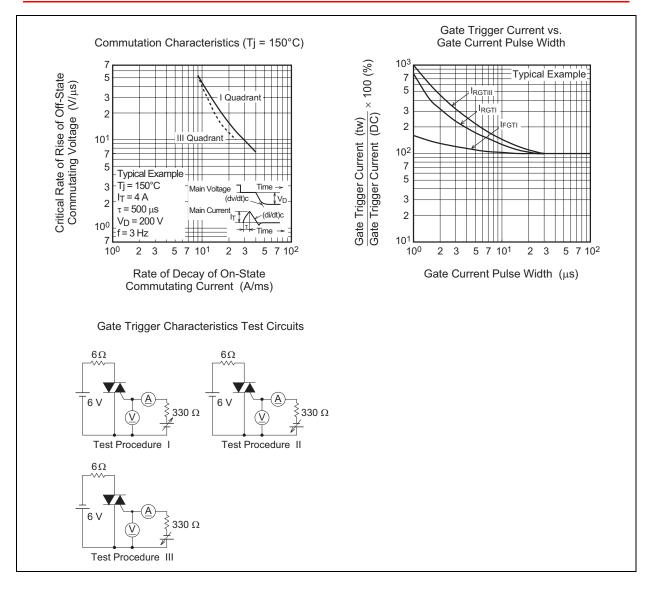
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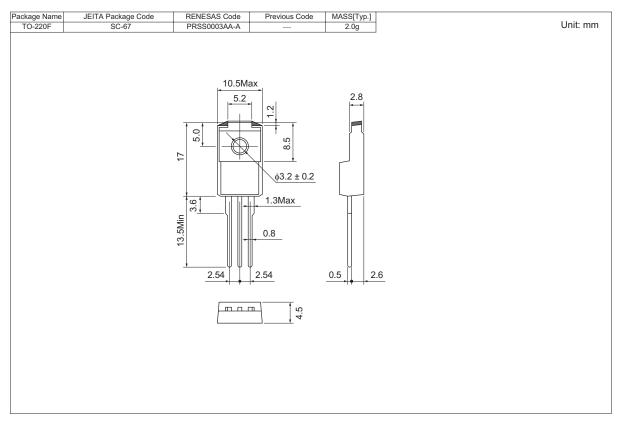
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Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR8PM-12LD
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR8PM-12LD-A8

Note : Please confirm the specification about the shipping in detail.

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http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

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